



8st February 2021

To Whomever It May Concern

This is an RFQ (Request for Quote) for Supply of Silicon wafers to be used for microelectronics applications (Quotes from Domestic manufacturers / vendors only).

Procedure:

- Vendors will be required to submit a quote, containing details of the Indian OEM with FOR - IISc Bengaluru price.**
- The technical description should take into account the following requirements and information that has been provided:

Wafer Spec	Quantity
Wafer #1: MATERIAL: SILICON Diameter: 76.2mm+/-0.5mm Growth Method: Cz Orientation: <1-0-0>+/-1° Type/Dopant: P/Boron Resistivity: 1-10 ohm-cm Thickness: 381+/-25 µm Front Surface: Polished Back Surface: Etched Flat(s):2 per SEMI standard	150 Nos.
Wafer #2 SILICON WAFERS Diameter:76.2+/-0.5 mm Growth Method: Cz Type/Dopant: N/Phos Orientation: <1-0-0>+/-1° Resistivity: 1-10 ohm-cm Thickness: 381+/-25 µm Front Surface: Polished Back Surface: Etched Flat(s):2 per SEMI standard	150 Nos.
Wafer #3 SILICON WAFERS	150 Nos.



<p>Diameter:76.2+/-0.5 mm Growth Method: Cz Type/Dopant: N/Phos Orientation: <1-0-0>+/-1° Resistivity: 1-100 ohm-cm Thickness: 381+/-25 µm Front Surface: Polished Back Surface: Etched Flat(s):2 per SEMI standard</p>	
<p>Wafer #4 MATERIAL: SILICON Diameter: 100mm+/-0.5mm Growth Method: Cz Orientation: <1-0-0>+/-1° Type/Dopant: P/Boron Resistivity: 1-100 ohm-cm Thickness: 525+/-25 µm Front Surface: Polished Back Surface: Etched</p>	150 Nos.
<p>Wafer #5 MATERIAL: SILICON Diameter: 100mm+/-0.5mm Growth Method: Cz Orientation: <1-0-0>+/-1° Type/Dopant: P/Boron Resistivity: 1-10 ohm-cm Thickness: 525+/-25 µm Front Surface: Polished Back Surface: Etched Flat(s):2 per SEMI standard</p>	150 Nos.
<p>Wafer #6 MATERIAL: SILICON Diameter: 100mm+/-0.5mm Growth Method: Cz Orientation: <1-0-0>+/-1° Type/Dopant: N/Phos Resistivity: 1-10 ohm-cm Thickness: 525+/-25 µm Front Surface: Polished Back Surface: Etched Flat(s):2 per SEMI standard</p>	150 Nos.



Wafer #7 MATERIAL: SILICON Diameter: 100mm+/-0.5mm Growth Method: Cz Orientation: <1-0-0>+/-1° Type/Dopant: N/Phos Resistivity: 1-100 ohm-cm Thickness: 525+/-25 µm Front Surface: Polished Back Surface: Etched Flat(s):2 per SEMI standard	150 Nos.
Wafer #8 Diameter: 50.8mm Orientation: <111> Type/Dopant: N/Phos Resistivity: 1-10 Ohm-cm Thickness: 300 ± 25µm Front Surface: Polished Back Surface: Etched Flat(s): 2 Per SEMI Standard	50 Nos.
Wafer #9 Diameter: 50.8mm Orientation: <110> Type/Dopant: N/Phos Resistivity: 1-10 Ohm-cm Thickness: 300 ± 25µm Front Surface: Polished Back Surface: Etched Flat(s): 2 Per SEMI Standard	50 Nos
Wafer #10 Diameter: 150 ±0.3 mm Orientation: <100> Type/Dopant: N/Phos Resistivity: 1-100 Ohm-cm Thickness: 625 ± 25µm Front Surface: Polished Back Surface: Etched Flat(s): 1 Primary Flat, SEMI-Std	150 Nos



3. The commercial comparison will be done as per Government of India rules, specifically GFR 2017. Note that GFR has recently been amended.
4. As per recent edits to the GFR, there are three classes of vendors distinguished by their “local content”. In the cover letter, vendors must mention which applies to them:
Class 1 supplier: Goods and services have a local content of equal to or more than 50%
Class 2 supplier: Goods and services have a local content more than 20% but less than 50%
Non-local supplier: Goods and services have a local content of equal to or less than 20%
5. Quotes will be entertained from Class 1 or Class 2 suppliers only.
6. The deadline for submission of quotes is the 19th February 2021, 5:30 pm Indian Standard Time. Proposals should arrive at the NNFC office, GF-20, Centre for Nano Science and Engineering, Indian Institute of Science, Bangalore 560012, India, by the above deadline
7. Please note: GST applicable to IISc will be 5 %. GST concessional certificate will be provided.

Thanking you,

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